

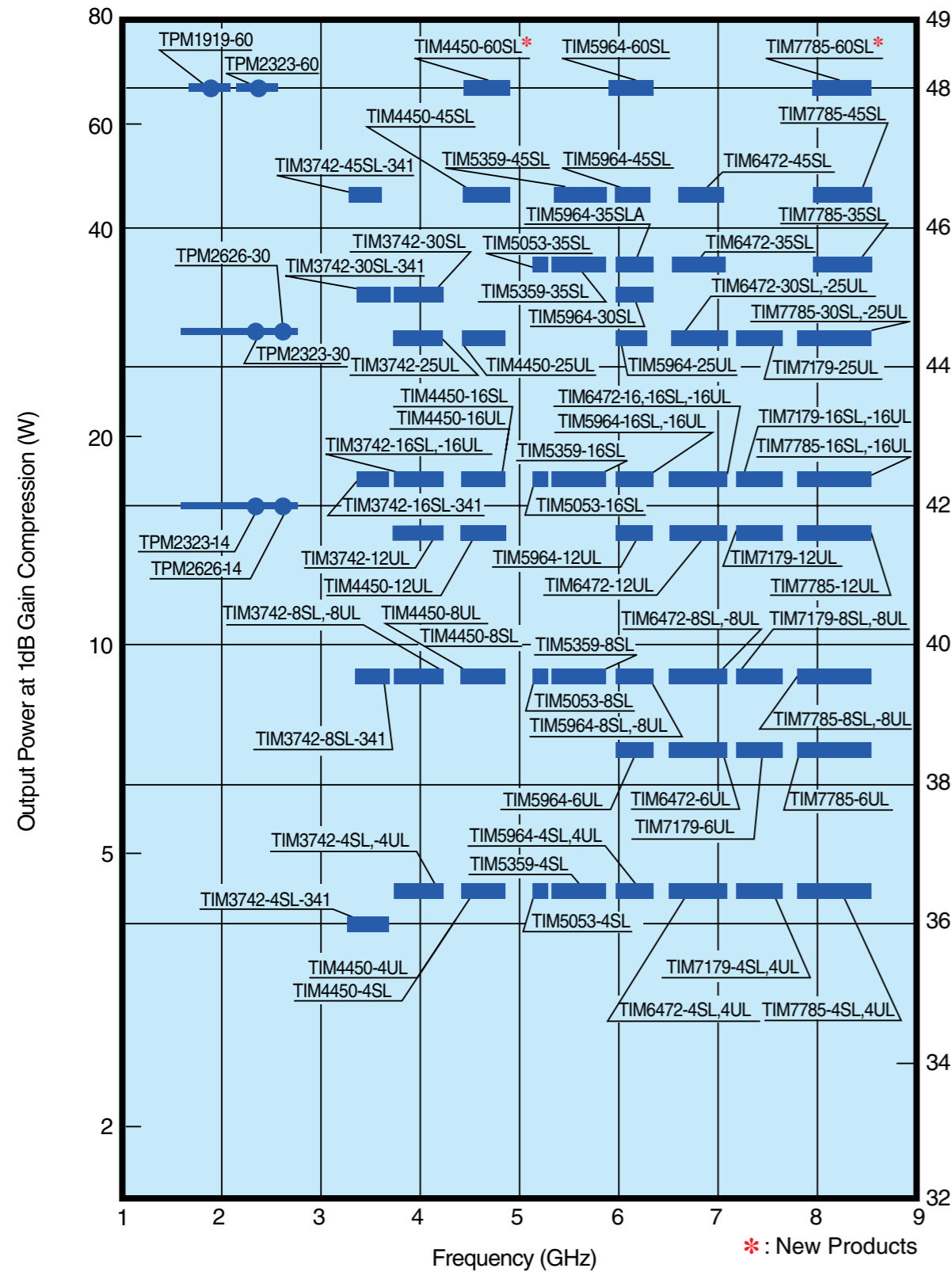


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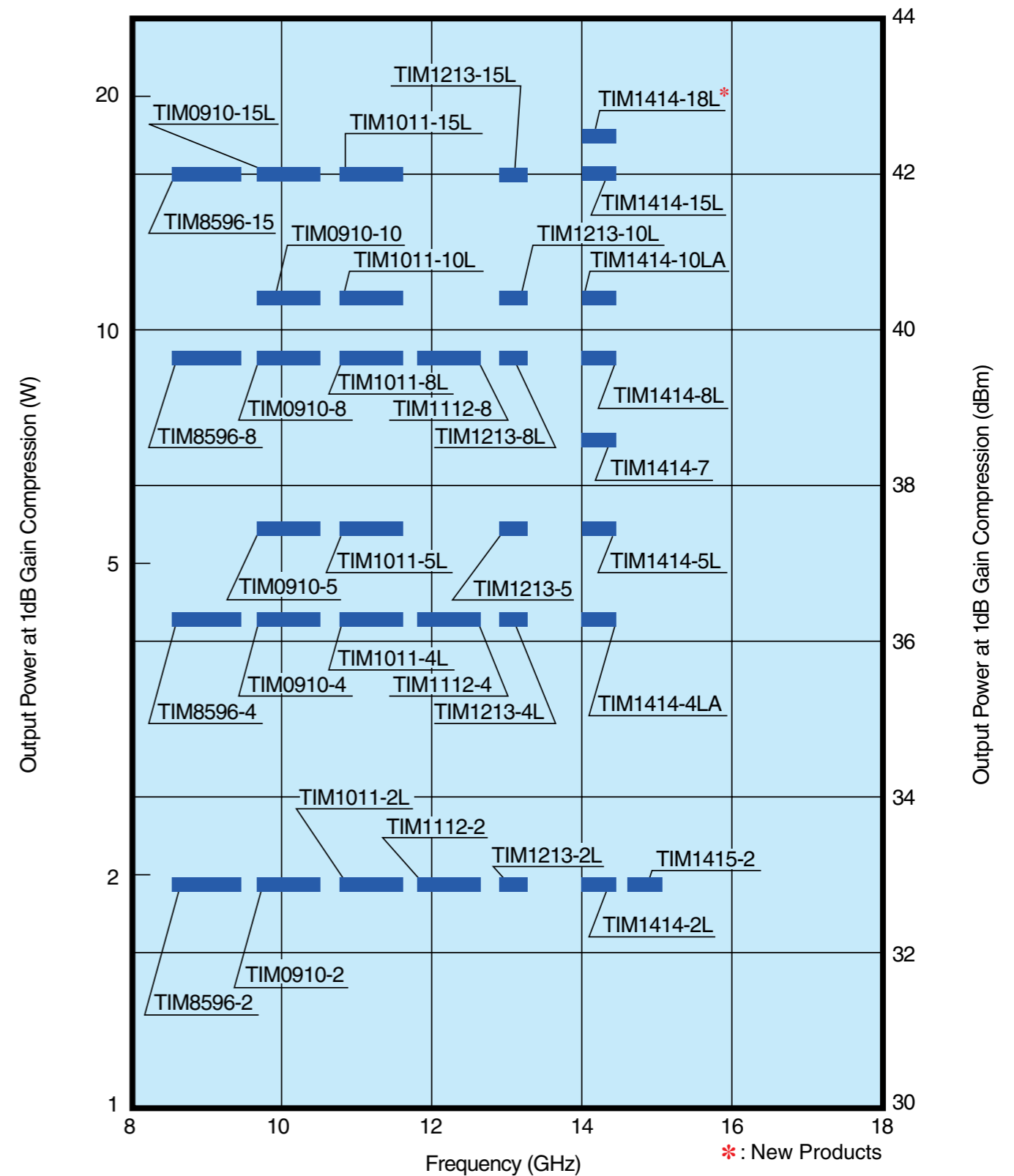
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Internally & Partially Matched Power GaAs FETs Pout-Frequency Map (L / S / C-band)



Internally Matched Power GaAs FETs Pout-Frequency Map (X / Ku-band)



Power GaAs FETs (Packaged)

FREQUENCY BAND (GHz)	TYPE No.	RF PERFORMANCE SPECIFICATIONS (Ta = 25 °C)						MAXIMUM			RATINGS (Ta = 25 °C)			ELECTRICAL CHARACTERISTICS (Ta = 25 °C)						PACKAGE CODE	TYPE No.			
		Ftest (GHz)	P _{1dB} (dBm)		G _{1dB} (dB)		η _{add} (%)	V _{DS} (V)	V _{GS} (V)	I _{DS} (A)	P _T (W) (Tc = 25 °C)	R _{th(c-c)} (°C/W) MAX./TYP.	Tch (°C)	gm (mS) TYP.	I _{DSS} (A)		V _{GSoff} (V) TYP.	@ V _{DS} = 3 V						
			MIN.	TYP.	MIN.	TYP.									TYP.	TYP.		TYP.	MAX.			TYP.	MAX.	I _{DS} (mA)
2-10	S8834	8	20.0	21.0	8.0	9.0	27	15	-5	0.125		1.5	100/50	175	30	0.045	0.09	0.125	-3.0	1.5	2-3H1B	S8834		
	S8835	8	23.0	24.0	7.0	8.0	26	15	-5	0.25		2.5	60/40	175	60	0.09	0.18	0.25	-3.0	3	2-3H1B	S8835		
	S8836A	8	28.5	29.5	6.5	7.5	30	15	-5	0.7		5.0	30/20	175	170	0.28	0.55	0.7	-3.5	5	2-7C1B	S8836A		
S8836B	2-3K1B		S8836B																					
6-9	S8837A	8	31.0	32.0	6.0	7.0	28	15	-5	1.4		7.5	20/13	175	350	0.55	1.1	1.4	-3.5	8	2-7C1B	S8837A		
2-18	S8850A	15	20.5	21.5	8.0	9.0	21	15	-5	0.125		1.0	150/90	175	30	0.045	0.1	0.125	-3.5	1.5	2-3K1B	S8850A		
			—	20.5 ■	—	9.0 ■	20 ■																	
	S8851	15	23.0	24.0	7.0	8.0	26	15	-5	0.25		2.0	75/40	175	60	0.09	0.2	0.25	-3.5	3	2-3K1B	S8851		
	S8853	15	27.0	28.0	6.0	7.0	25	15	-5	0.65		5.0	30/17	175	150	0.23	0.5	0.65	-3.5	8	2-3K1B	S8853		
	S8855	15	30.5	31.5	5.5	6.5	23	15	-5	1.3		9.0	16.7/10	175	300	0.5	1.0	1.3	-3.5	15	2-4J1B	S8855		

■ : V_{DS} = 8 V for S8850A



2-3H1B



2-3K1B



2-4J1B



2-7C1B

Power GaAs FETs (Chip Form)

FREQUENCY BAND (GHz)	TYPE No.	RF PERFORMANCE SPECIFICATIONS (Ta = 25 °C)						MAXIMUM			RATINGS (Ta = 25 °C)			ELECTRICAL CHARACTERISTICS (Ta = 25 °C)						REMARKS	TYPE No.				
		Ftest (GHz)	P1dB(dBm)		G1dB(dB)		$\eta_{add}(\%)$	VDS (V)	VGS (V)	IDS (A)	PT(W) (Tc = 25 °C)	Rth(c-c) (°C/W) MAX./TYP.	Tch (°C)	gm (mS) TYP.	IDSS(A)		VGSoff (V) TYP.	VGSoff (V)							
			@ VDS = 10 V, IDS = IDSS/2												@ VDS = 3 V			@ VDS = 3 V, VGS = 0 V				@ VDS = 3 V			
			MIN.	TYP.	MIN.	TYP.									TYP.	IDS(A)		TYP.	MAX.			IDS(mA)	IDS(mA)		
2-18	JS8850A-AS	15	20.5	21.5	8.0	9.0	21	15	- 5	0.125	1	150/90	175	30	0.045	0.1	0.125	- 3.5	1.5	CHIP	JS8850A-AS				
		18	—	20.5 ■	—	9.0 ■	20 ■															—	21.0	—	8.5
	JS8851-AS	15	23.0	24.0	7.0	8.0	26	15	- 5	0.25	2	75/40	175	60	0.09	0.2	0.25	- 3.5	3	CHIP	JS8851-AS				
		18	—	23.0	—	7.0	18																		
	JS8853-AS *	15	27.0	28.0	6.0	7.0	25	15	- 5	0.65	5	30/17	175	150	0.23	0.5	0.65	- 3.5	8	CHIP	JS8853-AS *				
		18	—	27.0	—	6.0	18																		
	JS8855-AS *	15	30.5	31.5	6.0	7.0	23	15	- 5	1.3	9	16.7/10	175	300	0.5	1.0	1.3	- 3.5	15	CHIP	JS8855-AS *				
		18	—	31.0	—	6.0	18																		

■ : VDS = 8 V for JS8850A-AS, * : Via-hole PHS Type



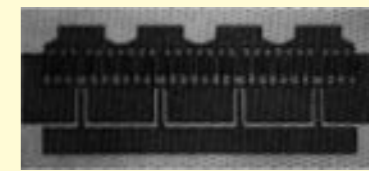
JS8850A-AS



JS8851-AS



JS8853-AS



JS8855-AS

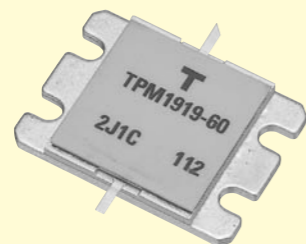
High Power and Low Distortion GaAs FETs (L / S-band)

FREQUENCY BAND (GHz)	TYPE No.	RF PERFORMANCE SPECIFICATIONS(Ta = 25 °C) @V _{DS} = 10 V								MAXIMUM RATINGS (Ta = 25 °C)				ELECTRICAL CHARACTERISTICS (Ta = 25 °C)					PACKAGE CODE	TYPE No.			
		P _{1dB} (dBm)		G _{1dB} (dB)		I _{DS} (A)		η _{add} (%)	ΔTch (°C)	V _{DS} (V)	V _{GS} (V)	I _{DS} (A)	P _T (W) (Tc = 25 °C)	R _{th(c-c)} (°C/W) MAX./TYP.	Tch (°C)	gm (mS)	I _{DSS} (A)				V _{GSoff} (V)	@V _{DS} = 3V	
		MIN.	TYP.	MIN.	TYP.	TYP.	MAX.										TYP.	MAX.				TYP.	MAX.
1.9	TPM1919-60▲	47.0●	48.0●	12.0●	13.0●	12.0●	15.0●	40●	100**	15	-5	46.0	185	0.8/0.6	175	20S	12.0	38.0	46.0	-1.8	300	2-16G6A	TPM1919-60▲
2.3	TPM2323-14▲	41.0	42.0	11.0	12.0	4.0	5.0	37	80**	15	-5	13.0	60.0	2.5/1.9	175	3200	3.5	10.0	13.0	-3.0	70	2-11D1B	TPM2323-14▲
	TPM2323-30▲	43.5	44.5	10.5	11.5	7.5	9.0	35	80**	15	-5	26.0	100.0	1.4/1.1	175	6300	7.0	20.0	26.0	-3.0	140	2-16G1B	TPM2323-30▲
	TPM2323-60▲	47.0◇	48.0◇	9.0◇	10.0◇	12.0◇	15.0◇	39◇	100**	15	-5	46.0	185	0.8/0.6	175	20S	12.0	38.0	46.0	-1.8	300	2-16G6A	TPM2323-60▲
2.6	TPM2626-14▲	41.0	42.0	11.0	12.0	4.0	5.0	37	80**	15	-5	13.0	60.0	2.5/1.9	175	3200	3.5	10.0	13.0	-3.0	70	2-11D1B	TPM2626-14▲
	TPM2626-30▲	44.0	44.5	10.5	11.5	7.5	9.0	35	80**	15	-5	26.0	100.0	1.4/1.1	175	6300	7.0	20.0	26.0	-3.0	140	2-16G1B	TPM2626-30▲

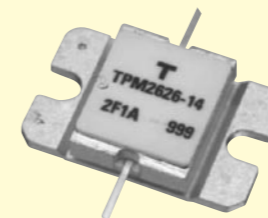
▲ : Partially Matched Type

● : V_{DS}=12 V, I_{DS}(RF off)=6 A(for TPM1919-60) ◇ : V_{DS}=12 V, I_{DS}(RF off)=8A(for TPM2323-60)

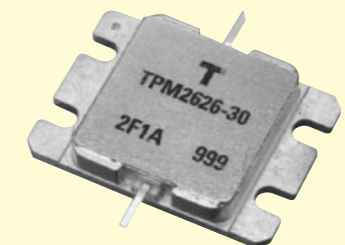
** : ΔTch=(10 V × I_{DS} + Pin - P_{1dB}) × R_{th(c-c)}(for TPM2323-14/-30, TPM2626-14/30), ΔTch=(12 V × I_{DS} + Pin - P_{1dB}) × R_{th(c-c)}(for TPM1919/2323-60)



2-16G6A



2-11D1B



2-16G1B

Internally Matched Power GaAs FETs (C-band) 3.3-3.6GHz band (WLL Applications)

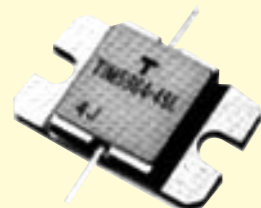
FREQUENCY BAND (GHz)	TYPE No.	RF PERFORMANCE SPECIFICATIONS (Ta = 25 °C) @V _{DS} = 10 V											MAXIMUM RATINGS (Ta = 25 °C)						ELECTRICAL CHARACTERISTICS (Ta = 25 °C)						PACKAGE CODE	TYPE No.
		P _{1dB} (dBm)		G _{1dB} (dB)		I _{DS} (A)		ΔG(dB) ^{***}	η _{add} (%)	IM ₃ (dBc) ^{**}		ΔTch*(°C)	V _{DS} (V)	V _{GS} (V)	I _{DS} (A)	P _T (W) (Tc = 25 °C)	R _{th(c-c)} (°C/W) MAX./TYP.	Tch(°C)	gm(mS)	I _{DSS} (A)		V _{GSoff} (V)	@V _{DS} = 3 V			
		MIN.	TYP.	MIN.	TYP.	TYP.	MAX.	MAX.	TYP.	MIN.	TYP.	MAX.	TYP.	TYP.	TYP.	TYP.	TYP.	TYP.	TYP.	TYP.	MAX.	TYP.	MAX.	TYP.		
3.3-3.6	TIM3742-4SL-341	35.5	36.5	10.0	—	1.1	1.3	± 0.6	37	-42●	-45●	80	15	-5	3.5	23	6.5/4.5	175	900	1.5	2.6	3.5	-2.5	15	2-11D1B	TIM3742-4SL-341
	TIM3742-8SL-341	38.5	39.5	10.0	—	2.2	2.6	± 0.6	36	-42▲	-45▲	80	15	-5	7.0	37.5	3.8/2.5	175	1800	3.0	5.2	7.0	-2.5	30	2-11D1B	TIM3742-8SL-341
	TIM3742-16SL-341	41.5	42.5	10.0	—	4.4	5.0	± 0.8	36	-42■	-45■	80	15	-5	14.0	75	2.0/1.5	175	3600	6.0	10.5	14.0	-2.5	60	2-16G1B	TIM3742-16SL-341
	TIM3742-30SL-341	44.0	45.0	10.0	—	7.0	8.0	± 0.8	42	-42◆	-45◆	100	15	-5	22.0	115	1.3/1.0	175	6300	10.0	18.0	22.0	-2.5	100	2-16G1B	TIM3742-30SL-341
	TIM3742-45SL-341	46.0	46.5	10.0	—	9.6	10.8	± 0.8	42	-42△	-45△	100	15	-5	26.0	125	1.2/0.8	175	8000	11.0	24.0	31.0	-2.5	170	2-16G1B	TIM3742-45SL-341

* : ΔTch=10 V X I_{DS} X R_{th(c-c)} ** : 2 tone test, single carrier level(Po) ● : 25.5 dBm ▲ : 28.5 dBm ■ : 31.5 dBm
◆ : 34.5 dBm △ : 35.5 dBm *** : Gain flatness

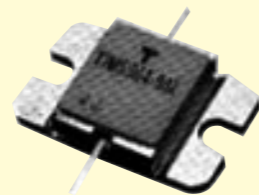
Internally Matched Power GaAs FETs (C-band) 5.85-6.75GHz band

FREQUENCY BAND (GHz)	TYPE No.	RF PERFORMANCE SPECIFICATIONS (Ta = 25 °C) @V _{DS} = 10 V											MAXIMUM RATINGS (Ta = 25 °C)						ELECTRICAL CHARACTERISTICS (Ta = 25 °C)						PACKAGE CODE	TYPE No.
		P _{1dB} (dBm)		G _{1dB} (dB)		I _{DS} (A)		ΔG(dB) ^{***}	η _{add} (%)	IM ₃ (dBc) ^{**}		ΔTch*(°C)	V _{DS} (V)	V _{GS} (V)	I _{DS} (A)	P _T (W) (Tc = 25 °C)	R _{th(c-c)} (°C/W) MAX./TYP.	Tch(°C)	gm(mS)	I _{DSS} (A)		V _{GSoff} (V)	@V _{DS} = 3 V			
		MIN.	TYP.	MIN.	TYP.	TYP.	MAX.	MAX.	TYP.	MIN.	TYP.	MAX.	TYP.	TYP.	TYP.	TYP.	TYP.	TYP.	TYP.	TYP.	TYP.	MAX.	TYP.	MAX.		
5.85-6.75	☆TIM5964-4SL-422	35.5	36.5	8.0	—	1.1	1.3	± 0.6	35	-42●	-45●	80	15	-5	3.5	23	6.5/4.5	175	900	1.5	2.6	3.5	-2.5	15	2-11D1B	☆TIM5964-4SL-422
	☆TIM5964-8SL-422	38.5	39.5	8.0	—	2.2	2.8	± 0.6	35	-42▲	-45▲	80	15	-5	7.0	37.5	3.8/2.5	175	1800	3.0	5.2	7.0	-2.5	30	2-11D1B	☆TIM5964-8SL-422
	☆TIM5964-16SL-422	41.5	42.5	8.0	—	4.4	5.0	± 0.8	34	-42■	-45■	80	15	-5	14.0	75	2.0/1.5	175	3600	6.0	10.5	14.0	-2.5	60	2-16G1B	☆TIM5964-16SL-422
	☆TIM5964-35SLA-422	45.0	45.5	8.0	—	8.0	9.0	± 0.8	39	-42○	-45○	100	15	-5	26.0	115	1.3/1.0	175	6500	10.5	20.0	26.0	-2.5	140	2-16G1B	☆TIM5964-35SLA-422

☆ : New Product * : ΔTch=10 V X I_{DS} X R_{th(c-c)} ** : 2 tone test, single carrier level(Po) ● : 25.5 dBm ▲ : 28.5 dBm ■ : 31.5 dBm
○ : 35 dBm *** : Gain flatness



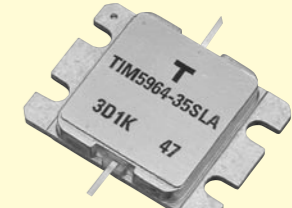
2-11D1B



2-11D1B



2-16G1B



2-16G1B